Applic. No.: 09/901,550

As shown in Fig. 4, the groove 7, 8 surrounds the bonding channel 6 and extends toward the bonding leads 5. --

In the Claims:

Claim 1 (amended). A support matrix for integrated semiconductors, comprising:

a frame having at least one bonding channel with an edge formed therein, said frame further having a groove formed therein along said edge of said bonding channel;

conductor track structures disposed on said frame, said groove formed in said frame functioning as a barrier for preventing a flow of a flowable material from said bonding channel onto said frame and onto said conductor track structures, said barrier having a region with a parting agent disposed thereon for repelling the flowable material; and

contacts, selected from the group consisting of bonding leads and wires, connected to said conductor track structures and disposed in said bonding channel, said contacts used for connecting said conductor track structures to an integrated circuit.

Claim 6 (amended). A support matrix for integrated semiconductors, comprising:

a frame having at least one bonding channel with an edge formed therein;

conductor track structures disposed on said frame, said frame and said conductor track structures having a groove formed therein along said edge of said bonding channel, said groove functioning as a barrier for preventing a flow of a flowable material from said bonding channel onto said frame and onto said conductor track structures, said barrier having a region with a parting agent disposed thereon for repelling the flowable material; and

contacts, selected from the group consisting of bonding leads and wires, connected to said conductor track structures and disposed in said bonding channel, said contacts used for connecting said conductor track structures to an integrated circuit.

Claim 8 (amended). A method for producing a support matrix for integrated semiconductors, which comprises the steps of:

providing a frame having conductor track structures disposed thereon, at least one bonding channel formed in the frame, and bonding leads disposed in the bonding channel and connected to

the conductor track structures for connecting the conductor track structures to an integrated semiconductor;

forming at least one groove along an edge of the bonding channel for preventing a flow of a flowable material from the bonding channel onto the frame and onto the conductor track structures; and

placing a parting agent in the groove for repelling the flowable material.